## S-8249 Series



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## **VOLTAGE MONITORING IC WITH CELL BALANCING FUNCTION**

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The S-8249 Series is a voltage monitoring IC with a cell balancing function and includes a high-accuracy voltage detection circuit and a delay circuit.

The S-8249 Series is suitable for cell balancing and overcharge protection of batteries and capacitors.

#### ■ Features

· High-accuracy voltage detection circuit

Cell balancing detection voltage: 2.0 V to 4.6 V (5 mV step)

Accuracy ±12 mV (2.0 V ≤ V<sub>BU</sub> < 2.4 V)

Accuracy  $\pm 0.5\%$  (2.4 V  $\leq$  V<sub>BU</sub>  $\leq$  4.6 V)

Cell balancing release voltage: 2.0 V to  $4.6 \text{ V}^{*1}$  Accuracy  $\pm 24 \text{ mV}$  ( $2.0 \text{ V} \le \text{V}_{BL} < 2.4 \text{ V}$ )

Accuracy  $\pm 1.0\%$  (2.4 V  $\leq$  V<sub>BL</sub>  $\leq$  4.6 V)

Overcharge detection voltage: 2.0 V to 4.6 V (5 mV step) Accuracy ±12 mV (2.0 V ≤ V<sub>CU</sub> < 2.4 V)

Accuracy  $\pm 0.5\%$  (2.4 V  $\leq$  V<sub>CU</sub>  $\leq$  4.6 V)

Overcharge release voltage: 2.0 V to 4.6 V\*2 Accuracy  $\pm 24$  mV (2.0 V  $\leq$  V<sub>CL</sub> < 2.4 V)

Accuracy  $\pm 1.0\%$  (2.4 V  $\leq$  V<sub>CL</sub>  $\leq$  4.6 V)

• Built-in Nch transistor with ON resistance of 5  $\Omega$  typ. between the CB pin and the VSS pin

Current consumption:
 2.0 μA max. (Ta = +25°C)

• Delay times are generated only by an internal circuit (External capacitors are unnecessary).

Nch open-drain output Active "H", active "L"

Switchable to power-saving mode by using the CE pin

• Operation temperature range: Ta = -40°C to +85°C

• Lead-free (Sn 100%), halogen-free

- \*1. Cell balancing release voltage = Cell balancing detection voltage Cell balancing hysteresis voltage (Cell balancing hysteresis voltage can be selected as 0 V or from a range of 0.1 V to 0.7 V in 50 mV step.)
- \*2. Overcharge release voltage = Overcharge detection voltage Overcharge hysteresis voltage (Overcharge hysteresis voltage can be selected as 0 V or from a range of 0.1 V to 0.7 V in 50 mV step.)

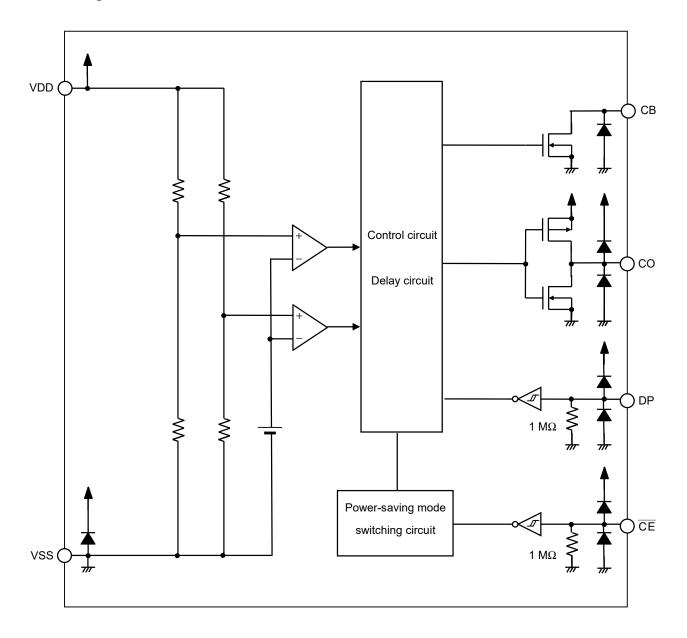
#### ■ Applications

- Rechargeable battery module
- Capacitor module

#### ■ Package

SOT-23-6

## ■ Block Diagram

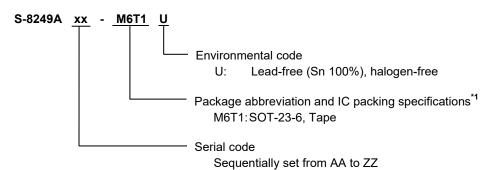


**\*1.** All diodes shown in the figure are parasitic diodes.

Figure 1

#### **■ Product Name Structure**

#### 1. Product name



\*1. Refer to the tape drawing.

#### 2. Package

**Table 1 Package Drawing Codes** 

Package Name	Dimension	Tape	Reel
SOT-23-6	MP006-A-P-SD	MP006-A-C-SD	MP006-A-R-SD

#### 3. Product name list

Table 2 (2 / 1)

				2 (2 / 1)			
	Cell Balancing Detection	Cell Balancing Release	Overcharge Detection	Overcharge Release	CO Pin	CO Pin	Combination of
Product Name	Voltage	Voltage	Voltage	Voltage	Output Form	Output Logic	Delay Time
	[V <sub>BU</sub> ]	[V <sub>BL</sub> ]	[Vcu]	[V <sub>CL</sub> ]	,	- 1 3	,
S-8249AAA-M6T1U	2.600 V	2.600 V	2.750 V	2.750 V	CMOS output	Active "H"	(1)
S-8249AAB-M6T1U	3.000 V	3.000 V	3.150 V	3.150 V	CMOS output	Active "H"	(1)
S-8249AAC-M6T1U	3.000 V	3.000 V	3.200 V	3.200 V	CMOS output	Active "H"	(1)
S-8249AAD-M6T1U	3.100 V	3.100 V	3.250 V	3.250 V	CMOS output	Active "H"	(1)
S-8249AAE-M6T1U	3.100 V	3.100 V	3.300 V	3.300 V	CMOS output	Active "H"	(1)
S-8249AAF-M6T1U	2.600 V	2.600 V	2.800 V	2.800 V	CMOS output	Active "H"	(1)
S-8249AAG-M6T1U	2.400 V	2.400 V	2.900 V	2.900 V	CMOS output	Active "H"	(1)
S-8249AAH-M6T1U	2.400 V	2.400 V	3.000 V	3.000 V	CMOS output	Active "H"	(1)
S-8249AAI-M6T1U	2.100 V	2.100 V	3.000 V	3.000 V	CMOS output	Active "H"	(1)
S-8249AAK-M6T1U	2.400 V	2.400 V	3.200 V	3.200 V	CMOS output	Active "H"	(1)
S-8249AAL-M6T1U	2.100 V	2.000 V	3.200 V	3.200 V	CMOS output	Active "H"	(1)
S-8249AAM-M6T1U	2.620 V	2.520 V	2.800 V	2.700 V	CMOS output	Active "H"	(1)
S-8249AAN-M6T1U	3.300 V	3.300 V	4.080 V	3.930 V	CMOS output	Active "H"	(1)
S-8249AAO-M6T1U	2.000 V	2.000 V	3.000 V	3.000 V	CMOS output	Active "H"	(1)
S-8249AAP-M6T1U	3.700 V	3.700 V	4.500 V	4.500 V	CMOS output	Active "H"	(1)
S-8249AAQ-M6T1U	3.800 V	3.800 V	4.080 V	3.930 V	CMOS output	Active "H"	(1)
S-8249AAR-M6T1U	2.800 V	2.800 V	3.150 V	3.150 V	CMOS output	Active "H"	(1)
S-8249AAS-M6T1U	2.800 V	2.800 V	3.200 V	3.200 V	CMOS output	Active "H"	(1)
S-8249AAT-M6T1U	2.800 V	2.800 V	3.100 V	3.100 V	CMOS output	Active "H"	(1)
S-8249AAU-M6T1U	2.500 V	2.400 V	3.800 V	3.700 V	CMOS output	Active "H"	(1)
S-8249AAV-M6T1U	2.300 V	2.200 V	3.800 V	3.700 V	CMOS output	Active "H"	(1)
S-8249AAW-M6T1U	2.650 V	2.600 V	2.750 V	2.650 V	Nch open-drain output	Active "L"	(1)
S-8249AAY-M6T1U	4.150 V	4.150 V	4.275 V	4.275 V	CMOS output	Active "H"	(2)

#### Table 2 (2 / 2)

Product Name	Cell Balancing Detection Voltage [V <sub>BU</sub> ]	Cell Balancing Release Voltage [V <sub>BL</sub> ]	Overcharge Detection Voltage [V <sub>CU</sub> ]	Overcharge Release Voltage [V <sub>CL</sub> ]	CO Pin Output Form	CO Pin Output Logic	Combination of Delay Time
S-8249ABA-M6T1U	3.650 V	3.550 V	3.800 V	3.500 V	CMOS output	Active "L"	(3)
S-8249ABB-M6T1U	4.350 V	4.350 V	4.425 V	4.325 V	CMOS output	Active "L"	(3)
S-8249ABC-M6T1U	4.200 V	4.200 V	4.300 V	4.200 V	CMOS output	Active "L"	(4)

Remark1. Please contact our sales representatives for products other than the above.

- 2. Set  $V_{CU} > V_{BU}$ .
- 3. Refer to Table 3 for details about combinations of delay times.

#### Table 3

Combination of Delay Time	Cell Balancing Detection Delay Time [tвu]	Cell Balancing Release Delay Time [t <sub>BL</sub> ]	Overcharge Detection Delay Time [tcu]	Overcharge Release Delay Time [tcL]
(1)	128 ms	1.0 ms	128 ms	1.0 ms
(2)	128 ms	1.0 ms	1024 ms	1.0 ms
(3)	64 ms	2.0 ms	256 ms	2.0 ms
(4)	64 ms	2.0 ms	256 ms	1.0 ms

**Remark** The delay times can be changed within the ranges listed above. For details, please contact our sales representatives.

Table 4

Delay Time	Symbol				Remark				
Cell balancing detection delay time*1	t <sub>BU</sub>	64 ms	128 r	ns*²	256 ms	512	2 ms	1024 ms	Select a value from the left.
Cell balancing release delay time	t <sub>BL</sub>	0.5 ms	S		1.0 ms*2		2.0 ms		Select a value from the left.
Overcharge detection delay time*1	t <sub>CU</sub>	64 ms	128 r	ns*²	256 ms	512	512 ms 1024 m		Select a value from the left.
Overcharge release delay time	t <sub>CL</sub>	0.5 m	S		1.0 ms*2	1.0 ms*2		2.0 ms	Select a value from the left.

<sup>\*1.</sup> Set  $t_{CU} \ge t_{BU}$ .

<sup>\*2.</sup> The value is the delay time of the standard products.

# ■ Pin Configuration

#### 1. SOT-23-6

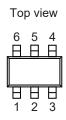


Figure 2

4

5

6

 $\overline{\mathsf{CE}}$ 

VDD

СВ

Pin No.	Symbol	Description
1	СО	Output pin for overcharge signal
2	VSS	Input pin for negative power supply
3	DP	Test mode switching pin "H": Test mode (used to shorten the delay time) "L": Normal operation mode
		Power-saving mode switching pin

"H": Power-saving mode

(Nch open-drain output)

"L": Normal operation mode

Input pin for positive power supply
Output pin for cell balancing signal

Table 5

## ■ Absolute Maximum Ratings

Table 6

(Ta = +25°C unless otherwise specified)

\(\text{\text{\$\pi_{\}}}}}}}}}}}}}}}}}}}}}}}}}}}}}}}}}}}}							
Item	Symbol	Applied Pin	Absolute Maximum Rating	Unit			
Input voltage between VDD pin and VSS pin	V <sub>DS</sub>	VDD	Vss - 0.3 to Vss + 6.0	٧			
Input pin voltage	VIN	CE, DP	$V_{SS} - 0.3 \text{ to } V_{DD} + 0.3 \le V_{SS} + 6.0$	V			
Output pin voltage	Vouт	CO, CB	$V_{SS} - 0.3 \text{ to } V_{DD} + 0.3 \le V_{SS} + 6.0$	<b>V</b>			
Output pin current	I <sub>CB</sub>	СВ	100 (-40°C to +85°C)	mA			
Operation ambient temperature	Topr	_	−40 to +85	°C			
Storage temperature	T <sub>stg</sub>	_	−55 to +125	°C			

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

#### **■** Thermal Resistance Value

Table 7

Item	Symbol	Symbol Condition			Тур.	Max.	Unit
			Board A	1	159	1	°C/W
			Board B	I	124	ı	°C/W
Junction-to-ambient thermal resistance*1	$\theta_{JA}$	SOT-23-6	Board C	1	_	1	°C/W
			Board D	_	_	_	°C/W
			Board E	_	_	_	°C/W

<sup>\*1.</sup> Test environment: compliance with JEDEC STANDARD JESD51-2A

Remark Refer to "■ Power Dissipation" and "Test Board" for details.

#### ■ Electrical Characteristics

For details about the test circuits and testing method, refer to "■ Test Circuit".

Caution Unless otherwise specified in Table 8, set V2 = V3 = 0 V, and SWn (n = 1 to 4) = OFF.

Table 8 (1 / 2)

(Ta = +25°C unless otherwise specified)

Item	Symbol		Condition	Min.	Тур.	Max.	Unit
Detection voltage							
Cell balancing detection	V <sub>BU</sub>	SW1 = ON	2.0 V ≤ V <sub>BU</sub> < 2.4 V		V <sub>BU</sub>	V <sub>BU</sub> + 0.012	V
voltage	<b>V</b> BU	SWT - ON	$2.4~V \leq V_{BU} \leq 4.6~V$	$V_{BU} \times 0.995$	$V_{\text{BU}}$	V <sub>BU</sub> × 1.005	V
Cell balancing release	$V_{BL}$	SW1 = ON	$2.0~V \leq V_{BL} < 2.4~V$	V <sub>BL</sub> – 0.024	$V_{BL}$	V <sub>BL</sub> + 0.024	V
voltage	V BL	3W1 - ON	$2.4~V \leq V_{BL} \leq 4.6~V$	V <sub>BL</sub> × 0.99	$V_{BL}$	V <sub>BL</sub> × 1.01	V
Overcharge detection	Vcu	2.0 V ≤ V <sub>CU</sub>	< 2.4 V	V <sub>CU</sub> - 0.012	Vcu	Vcu + 0.012	V
voltage	VCO	2.4 V ≤ V <sub>CU</sub>	≤ 4.6 V	V <sub>CU</sub> × 0.995	Vcu	V <sub>CU</sub> × 1.005	V
Overcharge release	VcL	2.0 V ≤ V <sub>CL</sub>	< 2.4 V	V <sub>CL</sub> - 0.024	VcL	V <sub>CL</sub> + 0.024	V
voltage	VCL	2.4 V ≤ V <sub>CL</sub>	≤ 4.6 V	V <sub>CL</sub> × 0.99	VcL	V <sub>CL</sub> × 1.01	V
Temperature coefficient						•	
Detection voltage temperature coefficient 1*1	$\frac{\Delta V_{BU}}{\Delta Ta \bullet V_{BU}}$	Ta = -40°C	to +85°C*3	I	100	350	ppm/ °C
Detection voltage temperature coefficient 2*2	ΔV <sub>CU</sub> ΔTa • V <sub>CU</sub>	Ta = -40°C	to +85°C*3	-	100	350	ppm/ °C
Input voltage							
Operation voltage between VDD pin and VSS pin	V <sub>DS</sub>	Voltages ou CB pin are	itput from CO pin and fixed	1.5	-	5.0	٧
CE pin voltage "H"	VCEH		_	-	-	$V_{DD} \times 0.9$	V
CE pin voltage "L"	VCEL		_	V <sub>DD</sub> × 0.1	_	_	V
DP pin voltage "H"	V <sub>DPH</sub>			ı	ı	V <sub>DD</sub> × 0.9	٧
DP pin voltage "L"	V <sub>DPL</sub>		_	V <sub>DD</sub> × 0.1	_	_	٧
Input current							
Current consumption during operation	I <sub>OPE</sub>	I <sub>VDD</sub> when \	/1 = V <sub>BL</sub> – 0.1 V	_	1.2	2.0	μА
Current consumption during power-saving	I <sub>PSV</sub>	I <sub>VDD</sub> when \	/1 = V2 = V <sub>BL</sub> - 0.1 V	-	-	0.1	μА

<sup>\*1.</sup> A change in the temperature of the detection voltage [mV/°C] is calculated by using the following equation.  $\frac{\Delta V_{BU}}{\Delta Ta} \left[ mV/^{\circ}C \right] = V_{BU} \left[ V \right] \times \frac{\Delta V_{BU}}{\Delta Ta} \left[ ppm/^{\circ}C \right] \div 1000$ 

\*2. A change in the temperature of the detection voltage [mV/°C] is calculated by using the following equation.  $\frac{\Delta V_{CU}}{\Delta Ta} \left[ \text{mV/°C} \right] = V_{CU} \left[ \text{V} \right] \times \frac{\Delta V_{CU}}{\Delta Ta \bullet V_{CU}} \left[ \text{ppm/°C} \right] \div 1000$ 

\*3. Since products are not screened at high and low temperature, the specification for this temperature range is guaranteed by design, not tested in production.

**Remark 1.**  $\frac{\Delta V_{BU}}{\Delta Ta}$ ,  $\frac{\Delta V_{CU}}{\Delta Ta}$ . Change in temperature of detection voltage

2. V<sub>BU</sub>, V<sub>CU</sub>: Set detection voltage

3.  $\frac{\Delta V_{BU}}{\Delta Ta \bullet V_{BU}}$ ,  $\frac{\Delta V_{CU}}{\Delta Ta \bullet V_{CU}}$ . Detection voltage temperature coefficient

Table 8 (2 / 2)

 $(Ta = +25^{\circ}C \text{ unless otherwise specified})$ 

			= +25°C ur		1	
Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Delay time	r		,		1	
Cell balancing detection delay time	t <sub>BU</sub>	_	$t_{\text{BU}}\times 0.8$	t <sub>BU</sub>	$t_{\text{BU}}  imes 1.2$	ms
Cell balancing release delay time	t <sub>BL</sub>	_	$t_{\text{BL}} \times 0.8$	t <sub>BL</sub>	$t_{\text{BL}} \times 1.2$	ms
Overcharge detection delay time	tcu	-	$t_{\text{CU}}\times 0.8$	tcu	tcu × 1.2	ms
Overcharge release delay time	tcL	_	$t_{\text{CL}} \times 0.8$	tcL	t <sub>CL</sub> × 1.2	ms
Output current						
CB pin output current						
CB pin sink current	Icвs	V1 = V <sub>BU</sub> + 0.1 V, SW2 = ON, V4 = 0.5 V	30	_	_	mA
CB pin leakage current	Icbl	V1 = V <sub>BL</sub> - 0.1 V, SW2 = ON, V4 = 6.0 V	_	_	0.1	μΑ
CO pin output current (out	put form:	CMOS output, output logic: acti	ve "H")		•	
CO pin sink current	Ісоь	V1 = V <sub>CL</sub> - 0.1 V, SW4 = ON, V5 = 0.5 V	5.0	-	_	mA
CO pin source current	Ісон	V1 = V <sub>CU</sub> + 0.1 V, SW4 = ON, V5 = V1 - 0.5 V	1.0	_	_	mA
CO pin output current (out	put form:	CMOS output, output logic: acti	ve "L")			
CO pin sink current	I <sub>COL</sub>	V1 = V <sub>CU</sub> + 0.1 V, SW4 = ON, V5 = 0.5 V	5.0	-	-	mA
CO pin source current	Ісон	V1 = V <sub>CL</sub> - 0.1 V, SW4 = ON, V5 = V1 - 0.5 V	1.0	-	-	mA
CO pin output current (out	put form:	Nch open-drain output, output le	ogic: activ	/e "H")	II.	
CO pin sink current	I <sub>COL</sub>	V1 = V <sub>CL</sub> - 0.1 V, SW4 = ON, V5 = 0.5 V	5.0	-	_	mA
CO pin leakage current	I <sub>COHL</sub>	V1 = V <sub>CU</sub> + 0.1 V, SW4 = ON, V5 = 6.0 V	_	-	0.1	μΑ
CO pin output current (out	put form:	Nch open-drain output, output le	ogic: activ	/e "L")		
CO pin sink current	I <sub>COL</sub>	V1 = V <sub>CU</sub> + 0.1 V, SW4 = ON, V5 = 0.5 V	5.0		_	mA
CO pin leakage current	Ісонь	V1 = V <sub>CL</sub> - 0.1 V, SW4 = ON, V5 = 6.0 V	_	_	0.1	μΑ

#### ■ Test Circuit

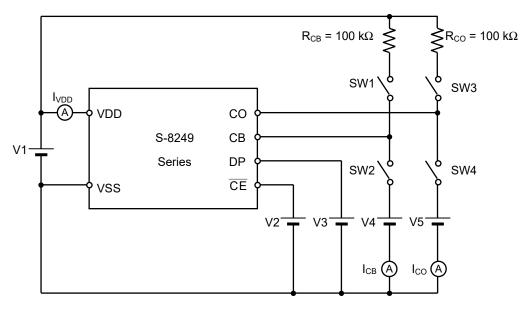


Figure 3

Caution Unless otherwise specified in Table 8, set V2 = V3 = 0 V, and SWn (n = 1 to 4) = OFF.

#### 1. CE pin voltage "H"

 $\overline{\text{CE}}$  pin voltage "H" ( $V_{\overline{\text{CEH}}}$ ) is defined as the voltage at which  $I_{VDD}$  is changed from  $I_{OPE}$  to  $I_{PSV}$  when V2 is increased from 0 V after setting V1 =  $V_{BL}$  – 0.1 V.

#### 2. CE pin voltage "L"

 $\overline{\text{CE}}$  pin voltage "L" (V<sub>CEL</sub>) is defined as the voltage at which I<sub>VDD</sub> is changed from I<sub>PSV</sub> to I<sub>OPE</sub> when V2 is decreased from V<sub>BL</sub> - 0.1 V after setting V1 = V2 = V<sub>BL</sub> - 0.1 V.

#### 3. DP pin voltage "H"\*1

DP pin voltage "H" ( $V_{DPH}$ ) is defined as the voltage at which the test mode is switched when V3 is increased from 0 V after setting V1 =  $V_{BL}$  – 0.1 V.

#### 4. DP pin voltage "L" \*1

DP pin voltage "L" ( $V_{DPL}$ ) is defined as the voltage at which the normal operation mode is switched when V3 is decreased from  $V_{BL}-0.1~V$  after setting V1 = V3 =  $V_{BL}-0.1~V$ .

#### 5. Cell balancing detection delay time

Cell balancing detection delay time ( $t_{BU}$ ) is defined as the time from when SW1 is set to ON and V1 is set to  $V_{BU}$  – 0.1 V to when the CB pin output is inverted after setting V1 to  $V_{BU}$  + 0.1 V.

#### 6. Cell balancing release delay time

Cell balancing release delay time ( $t_{BL}$ ) is defined as the time from when SW1 is set to ON and V1 is set to  $V_{BL}$  + 0.1 V to when the CB pin output is inverted after setting V1 to  $V_{BL}$  - 0.1 V.

#### 7. Overcharge detection delay time

Overcharge detection delay time ( $t_{CU}$ ) is defined as the time from when SW1 is set to ON and V1 is set to  $V_{CU}$  – 0.1 V to when the CO pin output is inverted after setting V1 to  $V_{CU}$  + 0.1 V.

#### 8. Overcharge release delay time

Overcharge release delay time ( $t_{CL}$ ) is defined as the time from when SW1 is set to ON and V1 is set to  $V_{CL}$  + 0.1 V to when the CO pin output is inverted after setting V1 to  $V_{CL}$  – 0.1 V.

\*1. For details about switching to the test mode by using the DP pin, refer to "5. DP pin" in "■ Operation".

#### ■ Standard Circuit

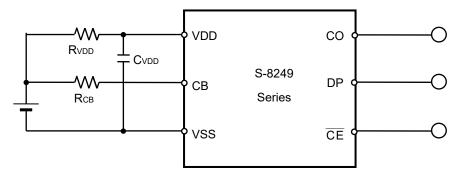


Figure 4

**Table 9 Constants for External Components** 

Symbol	Part	Purpose	Min.	Тур.	Max.	Remark
Rvdd	Resistor	esD protection, for power fluctuation control	150 Ω	330 Ω	1.0 kΩ	Resistance should be as small as possible to avoid worsening the overcharge detection accuracy due to current consumption.*1
C <sub>VDD</sub>	Capacitor	For power fluctuation control	0.068 μF	0.1 μF	1.0 μF	Connect a capacitor of 0.068 μF or more between VDD pin and VSS pin.*1
RcB	Resistor	For setting the cell balancing current value	ı	_	_	Set the required cell balancing current value depending on "2. Cell balancing status" in "■ Operation".*2

<sup>\*1.</sup> When connecting a resistor less than 150  $\Omega$  to R<sub>VDD</sub> or a capacitor less than 0.068  $\mu$ F to C<sub>VDD</sub>, the S-8249 Series may malfunction when power is largely fluctuated.

#### Cautions 1. The constants may be changed without notice.

2. It has not been confirmed whether the operation is normal or not in circuits other than the connection example. In addition, the connection example and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.

<sup>\*2.</sup> Set the cell balancing current value so that R<sub>CB</sub> does not exceed the power dissipation.

#### ■ Operation

Remark Refer to "■ Standard Circuit".

#### 1. Normal status

In the S-8249 Series, if the voltage between the VDD pin and the VSS pin  $(V_{DS})$  has not reached the cell balancing detection voltage  $(V_{BU})$ , the CB pin output is in the high-impedance status. The CO pin output status varies according to the output form and output logic selected, as shown in **Table 10**. This is the normal status.

CO Pin Output Form and Output Logic CB Pin Output CO Pin Output CMOS output, active "H" "H" "L"

CMOS output, active "L" "H" "H" "L"

Nch open-drain output, active "H" "H" "L"

Nch open-drain output, active "L"

Table 10

#### 2. Cell balancing status

In the S-8249 Series, if  $V_{DS}$  is  $V_{BU}$  or higher and this status continues for the cell balancing detection delay time ( $t_{BU}$ ) or longer, the CB pin output becomes "L". This is the cell balancing status.

"H"

"H"

The cell balancing status is released when  $V_{DS}$  drops to the cell balancing release voltage ( $V_{BL}$ ) or lower and this status continues for the cell balancing release delay time ( $t_{BL}$ ) or longer.

The S-8249 Series includes an Nch transistor with ON resistance of 5  $\Omega$  typ. (R<sub>CBON</sub>) between the CB pin and the VSS pin, thus causing the cell balancing current (I<sub>CB</sub>) to flow in cell balancing status, and the cell balancing operation to start.

By connecting a resistor ( $R_{CB}$ ) to the CB pin,  $I_{CB}$  in cell balancing status can be calculated by using the following equation.

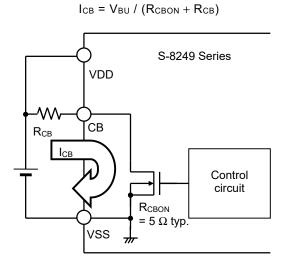


Figure 5

#### 3. Overcharge status

In the S-8249 Series, if  $V_{DS}$  is the overcharge detection voltage ( $V_{CU}$ ) or higher and this status continues for the overcharge detection delay time ( $t_{CU}$ ) or longer, the CO pin output is inverted. The CO pin output status varies according to the output form and output logic selected, as shown in **Table 11**. This is the overcharge status. In the overcharge status, the CB pin output becomes "L".

Table 11

CO Pin Output Form and Output Logic	CB Pin Output	CO Pin Output
CMOS output, active "H"	"L"	"H"
CMOS output, active "L"	"L"	"L"
Nch open-drain output, active "H"	"L"	"H"
Nch open-drain output, active "L"	"L"	"L"

The overcharge status is released when  $V_{DS}$  drops to the overcharge release voltage ( $V_{CL}$ ) or lower and this status continues for the overcharge release delay time ( $t_{CL}$ ) or longer.

#### 4. CE pin

The S-8249 Series has the  $\overline{\text{CE}}$  pin (Power-saving mode switching pin). The S-8249 Series is set to the power-saving mode by inputting a voltage of  $V_{\overline{\text{CEH}}}$  or higher to the  $\overline{\text{CE}}$  pin.

Table 12

CE Pin	Status	
Open (V <sub>CE</sub> = V <sub>SS</sub> )	Normal operation mode	
"H" (V <sub>CE</sub> ≥ V <sub>CEH</sub> )	Power-saving mode	
"L" $(V_{\overline{CE}} \leq V_{\overline{CE}L})$	Normal operation mode	

In the power-saving mode, the current consumption is decreased to current consumption during power-saving (I<sub>PSV</sub>). Also, in the power-saving mode, almost all operations are stopped, and the CB pin or the CO pin output in power-saving mode is the same as that in the normal status.

The  $\overline{CE}$  pin is pulled down to  $V_{SS}$  by the internal resistor. When in a mode other than power-saving mode, leave the  $\overline{CE}$  pin open or short it with  $V_{SS}$ .

#### 5. DP pin

The S-8249 Series has the DP pin (Test mode switching pin). The S-8249 Series is set to test mode (used to shorten the delay time) by inputting a voltage of  $V_{DPH}$  or higher to the DP pin.

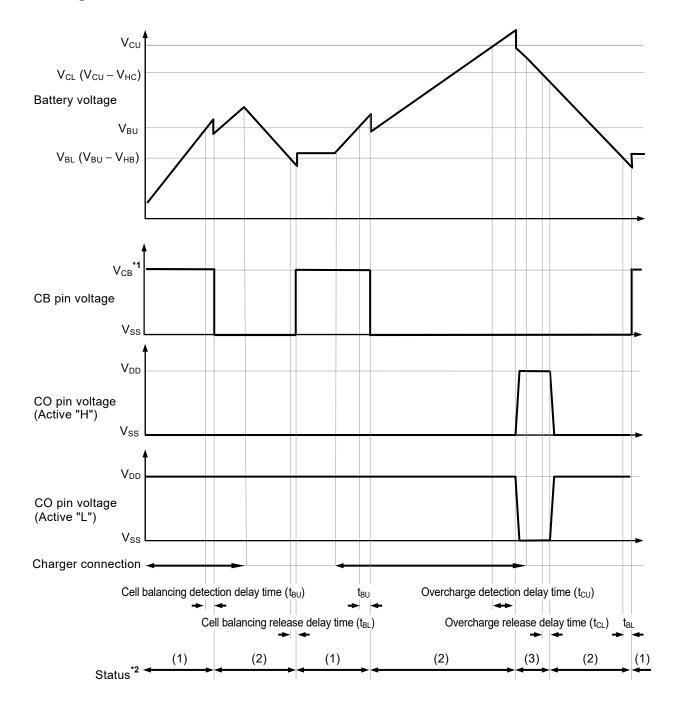
Table 13

DP Pin	Status	
Open (V <sub>DP</sub> = V <sub>SS</sub> )	Normal operation mode	
"H" (V <sub>DP</sub> ≥ V <sub>DPH</sub> )	Test mode	
"L" (V <sub>DP</sub> ≤ V <sub>DPL</sub> )	Normal operation mode	

In test mode, the cell balancing detection delay time ( $t_{BU}$ ) and overcharge detection delay time ( $t_{CU}$ ) are shortened to 1/64 of the delay time in the normal operation mode.

The DP pin is pulled down to  $V_{SS}$  by the internal resistor. When in a mode other than test mode, leave the DP pin open or short it with  $V_{SS}$ .

## **■** Timing Chart



- \*1. The CB pin is pulled up by the external resistor.
- \*2. (1): Normal status
  - (2): Cell balancing status
  - (3): Overcharge status

Remark The charger is assumed to charge with a constant current.

Figure 6

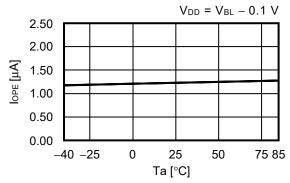
#### ■ Precautions

- The application conditions for the input voltage, output voltage, and load current should not exceed the power dissipation.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- ABLIC Inc. claims no responsibility for any and all disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

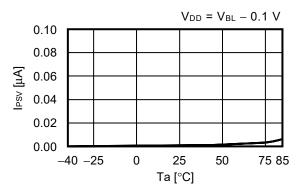
## ■ Characteristics (Typical Data)

#### 1. Current consumption

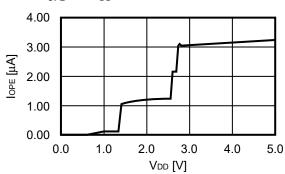
#### 1. 1 I<sub>OPE</sub> vs. Ta



1. 2 I<sub>PSV</sub> vs. Ta

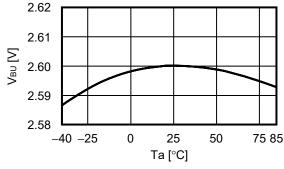


1. 3 IOPE vs. VDD

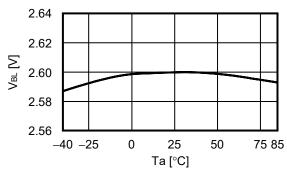


# 2. Cell balancing detection / release voltage, overcharge detection / release voltage and delay times

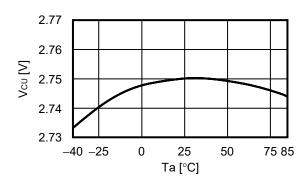
2. 1 V<sub>BU</sub> vs. Ta



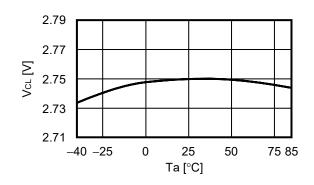
2. 2 V<sub>BL</sub> vs. Ta



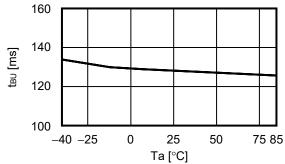
2. 3 V<sub>CU</sub> vs. Ta



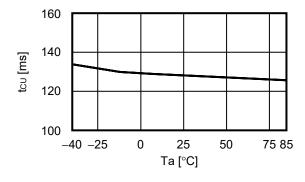
2. 4 V<sub>CL</sub> vs. Ta



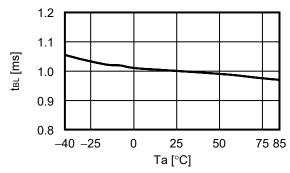
2. 5 t<sub>BU</sub> vs. Ta



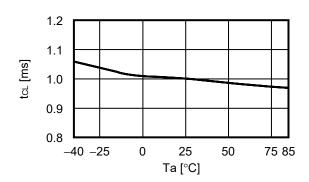
2. 7 tcu vs. Ta



2. 6 t<sub>BL</sub> vs. Ta

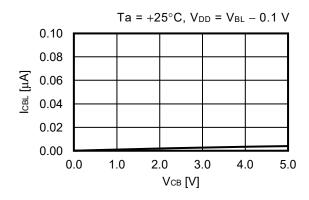


2. 8 tcl vs. Ta

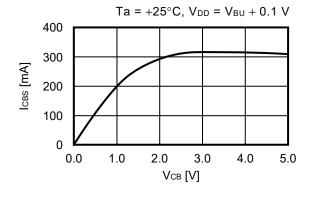


#### 3. Output current

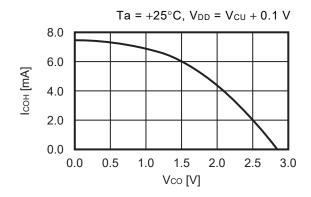
### 3. 1 I<sub>CBL</sub> vs. V<sub>CB</sub>



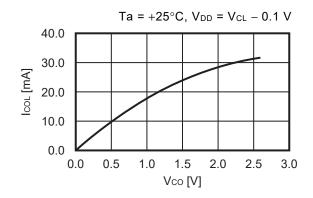
3. 2 ICBS VS. VCB



3. 3 Icon vs. Vco

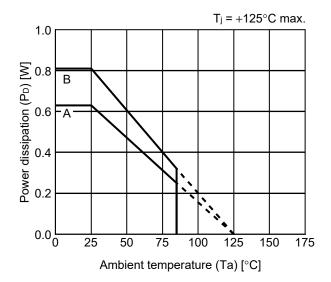


3. 4 Icol vs. Vco



## **■** Power Dissipation

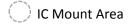
### SOT-23-6



Board	Power Dissipation (P <sub>D</sub> )
Α	0.63 W
В	0.81 W
С	_
D	_
E	_

# **SOT-23-3/3S/5/6** Test Board

## (1) Board A





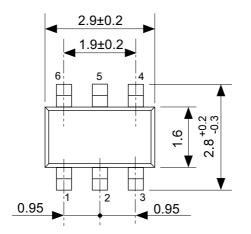
Item		Specification	
Size [mm]		114.3 x 76.2 x t1.6	
Material		FR-4	
Number of copper foil layer		2	
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070	
	2	-	
	3	-	
	4	74.2 x 74.2 x t0.070	
Thermal via		-	

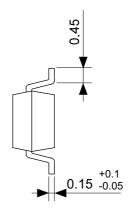
## (2) Board B

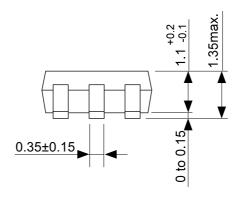


Item		Specification	
Size [mm]		114.3 x 76.2 x t1.6	
Material		FR-4	
Number of copper foil layer		4	
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070	
	2	74.2 x 74.2 x t0.035	
	3	74.2 x 74.2 x t0.035	
	4	74.2 x 74.2 x t0.070	
Thermal via		-	

No. SOT23x-A-Board-SD-2.0

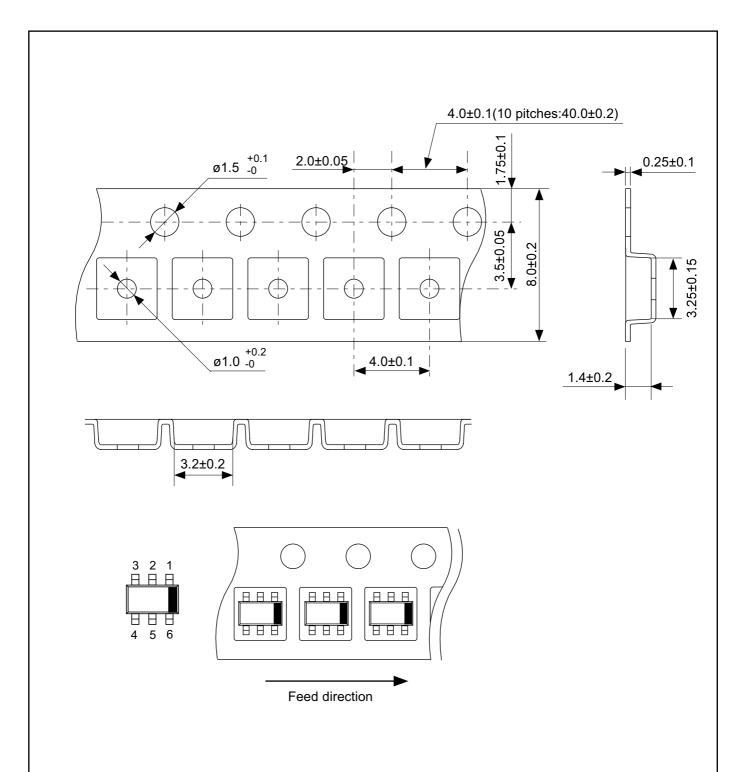






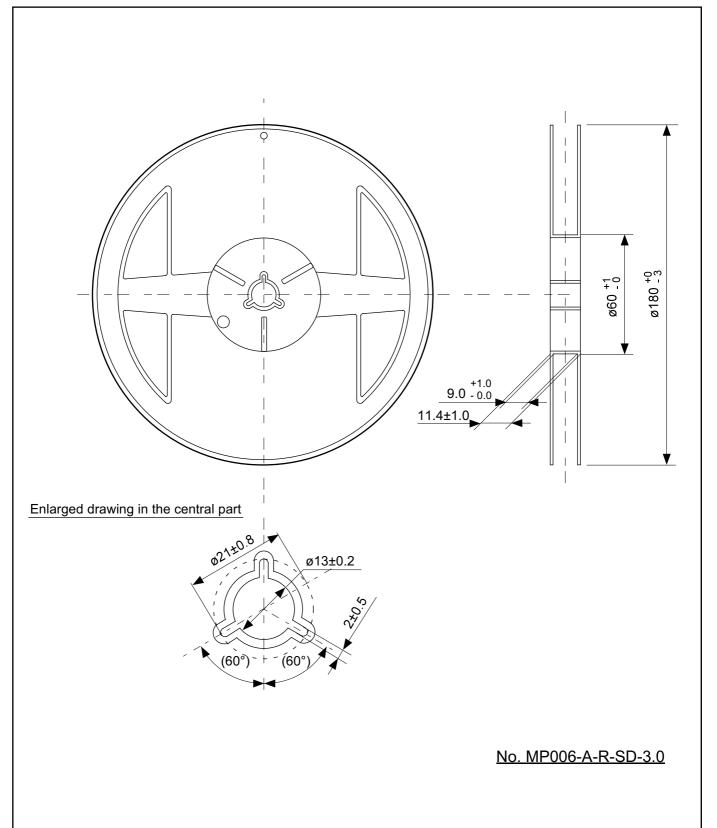
## No. MP006-A-P-SD-2.1

TITLE	SOT236-A-PKG Dimensions	
No.	MP006-A-P-SD-2.1	
ANGLE	<b>\$</b>	
UNIT	mm	
ABLIC Inc.		



## No. MP006-A-C-SD-3.1

TITLE	SOT236-A-Carrier Tape	
No.	MP006-A-C-SD-3.1	
ANGLE		
UNIT	mm	
ABLIC Inc.		



TITLE	SOT236-A-Reel		
No.	MP006-A-R-SD-3.0		
ANGLE		QTY	3,000
UNIT	mm		
ABLIC Inc.			

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